

Table of Contents

Preface, Committees, Sponsors and Overview

Chapter 1: SiC Bulk Growth

1.1 PVT and CVD

Open Issues in SiC Bulk Growth

D. Chaussende, K. Ariyawong, N. Tsavdaris, M. Seiss, Y.J. Shin, J.M. Dedulle, R. Madar, E. Sarigiannidou, J. La Manna, O. Chaix-Pluchery and T. Ouisse

3

Real-Time Measurement of the Evolution of Growth Facets during SiC PVT Bulk Growth

Using 3-D X-Ray Computed Tomography

G. Neubauer, M. Salamon, N. Uhlmann and P.J. Wellmann

9

Effect of Facet Occurrence on Polytipe Destabilization during Bulk Crystal Growth of SiC by Seeded Sublimation

N. Tsavdaris, K. Ariyawong, O. Chaix-Pluchery, J.M. Dedulle, E. Sarigiannidou and D. Chaussende

13

Development of RAF Quality 150mm 4H-SiC Wafer

H. Kondo, H. Takaba, M. Yamada, Y. Urakami, T. Okamoto, M. Kobayashi, T. Masuda, I. Gunjishima, K. Shigeto, N. Ooya, N. Sugiyama, A. Matsuse, T. Kozawa, T. Sato, F. Hirose, S. Yamauchi and S. Onda

17

Impurity Behavior of High Purity SiC Powder during SiC Crystal Growth

D.G. Shin, H.R. Son, S. Heo, B.S. Kim, J.E. Han, K.S. Min and D.H. Lee

22

Effect of TaC-Coated Crucible on SiC Single Crystal Growth

D.H. Lee, H.T. Lee, B.J. Bae, H.J. Lee, S.I. Lee, M.S. Park, W.J. Lee, I.G. Yeo, T.H. Eun and M.C. Chun

26

Interaction between Vapor Species and Graphite Crucible during the Growth of SiC by PVT

K. Ariyawong, N. Tsavdaris, J.M. Dedulle, E. Sarigiannidou, T. Ouisse and D. Chaussende

31

Comparison of Thermodynamic Databases for the Modeling of SiC Growth by PVT

K. Ariyawong, E. Blanquet, J.M. Dedulle, T. Ouisse and D. Chaussende

35

Spiral Step Dissociation on PVT Grown SiC Crystals

M. Seiss, T. Ouisse and D. Chaussende

39

Reciprocal Space Mapping Studies of the Initial Stage of the PVT Growth of 4H-SiC Crystals Parallel and Perpendicular to the *c*-Axis

C. Ohshige, T. Takahashi, N. Ohtani, M. Katsuno, T. Fujimoto, S. Sato, H. Tsuge, T. Yano, H. Matsuhata and M. Kitabatake

43

Growth of Low Resistivity n-Type 4H-SiC Bulk Crystals by Sublimation Method Using Co-Doping Technique

T. Kato, K. Eto, S. Takagi, T. Miura, Y. Urakami, H. Kondo, F. Hirose and H. Okumura

47

4H-SiC Bulk Growth Using High-Temperature Gas Source Method

Y. Tokuda, J. Kojima, K. Hara, H. Tsuchida and S. Onda

51

Fast 4H-SiC Crystal Growth by High-Temperature Gas Source Method

N. Hoshino, I. Kamata, Y. Tokuda, E. Makino, J. Kojima and H. Tsuchida

55

Dislocation Analysis of 4H-SiC Crystals Obtained at Fast Growth Rate by the High-Temperature Gas Source Method

I. Kamata, N. Hoshino, Y. Tokuda, E. Makino, J. Kojima and H. Tsuchida

59

1.2 Solution Growth

Increase in the Growth Rate by Rotating the Seed Crystal at High Speed during the Solution Growth of SiC

T. Umezaki, D. Koike, A. Horio, S. Harada and T. Ujihara

63

Surface Morphology and Threading Dislocation Conversion Behavior during Solution Growth of 4H-SiC Using Al-Si Solvent

S. Harada, Y. Yamamoto, S. Xiao, M. Tagawa and T. Ujihara

67

Electromagnetic Enhancement of Carbon Transport in SiC Solution Growth Process: A Numerical Modeling Approach	
K. Ariyawong, J.M. Dedulle and D. Chaussende	71
Solution Growth of <i>p</i>-Type 4H-SiC Bulk Crystals with Low Resistivity	
T. Shirai, K. Danno, A. Seki, H. Sakamoto and T. Bessho	75
Top-Seeded Solution Growth of 3 Inch Diameter 4H-SiC Bulk Crystal Using Metal Solvents	
K. Kusunoki, K. Kamei, N. Okada, K. Moriguchi, H. Kaido, H. Daikoku, M. Kado, K. Danno, H. Sakamoto, T. Bessho and T. Ujihara	79
 Chapter 2: SiC Epitaxial Growth	
2.1 Homoeptaxial Growth	
Evolution of Fast 4H-SiC CVD Growth and Defect Reduction Techniques	
H. Tsuchida, I. Kamata, M. Ito, T. Miyazawa, N. Hoshino, H. Fujibayashi, H. Ito, M. Naitou, H. Aoki, K. Nishikawa, E. Makino, Y. Tokuda and J. Kojima	85
Demonstration of High Quality 4H-SiC Epitaxial Growth with Extremely Low Basal Plane Dislocation Density	
T. Tanaka, N. Kawabata, Y. Mitani, N. Tomita, M. Tarutani, T. Kuroiwa, Y. Toyoda, M. Imaizumi, H. Sumitani and S. Yamakawa	91
Effects of the Growth Rate on the Quality of 4H Silicon Carbide Films for MOSFET Applications	
M. Camarda, S. Privitera, R. Anzalone, N. Piluso, P. Fiorenza, A. Alberti, G. Pellegrino, A. La Magna, F. La Via, C. Vecchio, M. Mauceri, G. Litrico, A. Pecora and D. Crippa	95
Conversion of Basal Plane Dislocations to Threading Edge Dislocations in Growth of Epitaxial Layers on 4H-SiC Substrates with a Vicinal Off-Angle	
K. Masumoto, S. Ito, H. Goto, H. Yamaguchi, K. Tamura, C. Kudou, J. Nishio, K. Kojima, T. Ohno and H. Okumura	99
Progress in Large-Area 4H-SiC Epitaxial Layer Growth in a Warm-Wall Planetary Reactor	
B. Thomas, D.M. Hansen, J. Zhang, M.J. Loboda, J. Uchiyama, T.J. Toth, G.Y. Chung, I. Manning, J.P. Quast and S.G. Mueller	103
C-Face Epitaxial Growth of 4H-SiC on Quasi-150-mm Diameter Wafers with High Throughput	
J. Nishio, C. Kudou, K. Tamura, K. Masumoto, K. Kojima and T. Ohno	109
Latest SiC Epitaxial Layer Growth Results in a High-Throughput 6×150 mm Warm-Wall Planetary Reactor	
A.A. Burk, D. Tsvetkov, M.J. O'Loughlin, S. Ustin, L. Garrett, A.R. Powell, J. Seaman and N. Partin	113
Fast 4H-SiC Epitaxial Growth on 150 mm Diameter Area with High-Speed Wafer Rotation	
H. Fujibayashi, M. Ito, H. Ito, I. Kamata, M. Naitou, K. Hara, S. Yamauchi, K. Suzuki, M. Yajima, S.I. Mitani, K. Suzuki, H. Aoki, K. Nishikawa, T. Kozawa and H. Tsuchida	117
4H-SiC Epitaxial Layer Grown on 150 mm Automatic Horizontal Hot Wall Reactor PE106	
M. Mauceri, A. Pecora, G. Litrico, C. Vecchio, M. Puglisi, D. Crippa, N. Piluso, M. Camarda and F. La Via	121
Development of Homoeptaxial Growth Technique on 4H-SiC Vicinal Off Angled Substrate	
K. Kojima, K. Masumoto, S. Ito, A. Nagata and H. Okumura	125
Homo-Epitaxial Growth on Low-Angle Off Cut 4H-SiC Substrate	
X. Li, E. Janzén and A. Henry	131
Epitaxial Growth of Thick Multi-Layer 4H-SiC for the Fabrication of Very High-Voltage C-Face n-Channel IGBT	
T. Miyazawa, S. Ji, K. Kojima, Y. Ishida, K. Nakayama, A. Tanaka, K. Asano and H. Tsuchida	135
Dependence of the Growth Parameters on the In-Plane Distribution of 150 mm φ Size SiC Epitaxial Wafer	
C. Kudou, K. Tamura, J. Nishio, K. Masumoto, K. Kojima and T. Ohno	139
Comparative Study of Defects in 4H-SiC Epilayers Grown on 4° Off-Axis (0001) and (000-1) Substrates	
T. Aigo, W. Itoh, T. Fujimoto and T. Yano	143
An Approach to Trace Defects Propagation during SiC Epitaxy	
Y.M. Fan, L.G. Zhang, J. Wang, X.M. Zhang, Z.H. Zhang, B.S. Zhang and T.S. Sudarshan	147

Characterization of the Defect Evolution in Thick Heavily Al-Doped 4H-SiC Epilayers S. JI, K. Kojima, Y. Ishida, H. Yamaguchi, S. Saito, T. Kato, H. Tsuchida, S. Yoshida and H. Okumura	151
Crystal Growth of Highly Oriented Silicon Carbide by Chemical Vapor Deposition with Alternating Gas Supply T. Nagano and K. Sato	155
Effect of Process Parameters on Dislocation Density in Thick 4H-SiC Epitaxial Layers Grown by Chloride-Based CVD on 4° Off-Axis Substrates M. Yazdanfar, H. Pedersen, O. Kordina and E. Janzén	159
50 µm-Thick 100 mm 4H-SiC Epitaxial Layer Growth by Warm-Wall Planetary Reactor Y.Q. Sun, G. Feng, Z.Y. Li, L.P. Lv, J.Y. Luo, J.B. Wu, Y.Y. Li and J.H. Zhang	163
Demonstration of High Quality 4H-SiC Epitaxy by Using the Two-Step Growth Method Y. Mitani, N. Tomita, K. Hamano, M. Tarutani, T. Tanaka, A. Ohno, T. Kuroiwa, Y. Toyoda, M. Imaizumi, H. Sumitani and S. Yamakawa	167
Simulation Study of High-Speed Wafer Rotation Effects in a Vertical Reactor for 4H-SiC Epitaxial Growth on 150 mm Substrates M. Ito, H. Fujibayashi, H. Ito, I. Kamata, M. Naito, K. Hara, S. Yamauchi, K. Suzuki, M. Yajima, S.I. Mitani, K. Suzuki, H. Aoki, K. Nishikawa, T. Kozawa and H. Tsuchida	171
Revisiting the Thermochemical Database of Si-C-H System Related to SiC CVD Modeling P. Sukkaew, L. Ojamäe, Ö. Danielsson, O. Kordina and E. Janzén	175
Fast Growth Rate Epitaxy on 4° Off-Cut 4-Inch Diameter 4H-SiC Wafers J. Hassan, H.T. Bae, L. Lilja, I. Farkas, I. Kim, P. Stenberg, J.W. Sun, O. Kordina, P. Bergman, S.Y. Ha and E. Janzén	179
Simulation Studies on Giant Step Bunching in 4H-SiC Epitaxial Growth: Cluster Effect Y. Ishida and S. Yoshida	183
Ge Assisted SiC Epitaxial Growth by CVD on SiC Substrate K. Alassaad, V. Soulière, B. Doisneau, F. Cauwet, H. Peyre, D. Carole, D. Chaussende and G. Ferro	187
4H-SiC Epitaxial Growth on C-Face 150 mm SiC Substrate A. Miyasaka, J. Norimatsu, K. Fukada, Y. Tajima, Y. Kageshima, D. Muto, M. Odawara, T. Okano, K. Momose, Y. Osawa, H. Osawa and T. Sato	193
Study of Surface Morphologies of On-Axis 6H-SiC Wafer after High-Temperature Etching and Epitaxial Growth X.C. Liu, B. Shi, J. Xin, W. Huang, X. Liu, Y.Q. Zheng and E.W. Shi	197
First-Principles Study of Nanofacet Formation on 4H-SiC(0001) Surface K. Sawada, J.I. Iwata and A. Oshiyama	201
Improved Epilayer Surface Morphology on 2° Off-Cut 4H-SiC Substrates L. Lilja, J. Hassan, E. Janzén and J.P. Bergman	206
HCl Assisted Growth of Thick 4H-SiC Epilayers for Bipolar Devices B. Kallinger, C. Ehlers, P. Berwian, M. Rommel and J. Friedrich	210
Homo-Epitaxial Growth on 2° Off-Cut 4H-SiC(0001) Si-Face Substrates Using H₂-SiH₄-C₃H₈ CVD System K. Tamura, C. Kudou, K. Masumoto, J. Nishio and K. Kojima	214
Simulations of SiC CVD - Perspectives on the Need for Surface Reaction Model Improvements Ö. Danielsson, O. Kordina and E. Janzén	218
Simulation Studies on Giant Step Bunching Accompanying Trapezoid-Shape Defects in 4H-SiC Epitaxial Layer Y. Ishida and S. Yoshida	222

2.2 Heteroepitaxial Growth

Heteroepitaxial CVD Growth of 3C-SiC on Diamond Substrate V. Soulière, A. Vo-Ha, D. Carole, A. Tallaire, O. Brinza, J.C. Pinero, D. Araújo and G. Ferro	226
The Influence of the Carbonization Mechanisms on the Crystalline Quality of the Carbonization Layer for Heteroepitaxial Growth of 3C-SiC Y. Watanabe, T. Horikawa and K. Kamimura	230
3C-SiC Seeded Growth on Diamond Substrate by VLS Transport A. Vo-Ha, M. Rebaud, D. Carole, M. Lazar, A. Tallaire, V. Soulière, J.C. Pinero, D. Araújo and G. Ferro	234

Monte Carlo Study of the Early Growth Stages of 3C-SiC on Misoriented and 6H-SiC Substrates	
M. Camarda, A. La Magna and F. La Via	238
Optical Investigation of 3C-SiC Hetero-Epitaxial Layers Grown by Sublimation Epitaxy under Gas Atmosphere	
P. Kwasnicki, V. Jokubavicius, J.W. Sun, H. Peyre, R. Yakimova, M. Syväjärvi, J. Camassel and S. Juillaguet	243
A Study of the Intermediate Layer in 3C-SiC/6H-SiC Heterostructures	
A.A. Lebedev, M.V. Zamoryanskaya, S.Y. Davydov, D.A. Kirilenko, S.P. Lebedev, L.M. Sorokin, D.B. Shustov and M.P. Shcheglov	247
Formation of an Interfacial Buffer Layer for 3C-SiC Heteroepitaxy on AlN/Si Substrates	
K. Meguro, T. Narita, K. Noto and H. Nakazawa	251
Curvature Evaluation of Si/3C-SiC/Si Hetero-Structure Grown by Chemical Vapor Deposition	
R. Anzalone, M. Camarda, A. Severino, N. Piluso and F. La Via	255

Chapter 3: Physical Properties and Characterization of SiC

3.1 Intrinsic Point Defects and Carrier Lifetime

Characterization of Ge-Doped Homoepitaxial Layers Grown by Chemical Vapor Deposition	
T. Sledziewski, S. Beljakowa, K. Alissaad, P. Kwasnicki, R. Arvinte, S. Juillaguet, M. Zielinski, V. Soulière, G. Ferro, H.B. Weber and M. Krieger	261
Persistent Conductivity in n-Type 3C-SiC Observed at Low Temperatures	
S. Beljakowa, M. Hauck, M. Bockstedte, F. Fromm, M. Hundhausen, H. Nagasawa, H.B. Weber, G. Pensl and M. Krieger	265
Minority Carrier Transient Spectroscopy of As-Grown, Electron Irradiated and Thermally Oxidized p-Type 4H-SiC	
G. Alfieri and T. Kimoto	269
Annealing of Electron Irradiated, Thick, Ultrapure 4H SiC between 1100°C and 1500°C and Measurements of Lifetime and Photoluminescence	
W.M. Klahold, R.P. Devaty, W.J. Choyke, K. Kawahara, T. Kimoto and T. Ohshima	273
Identification of Structures of the Deep Levels in 4H-SiC	
H. Nakane, M. Kato, M. Ichimura and T. Ohshima	277
Oxidation Induced ON₁, ON_{2a/b} Defects in 4H-SiC Characterized by DLTS	
I.D. Booker, H. Abdalla, L. Lilja, J. Hassan, P. Bergman, E.Ö. Sveinbjörnsson and E. Janzén	281
Identification of the Negative Carbon Vacancy at Quasi-Cubic Site in 4H-SiC by EPR and Theoretical Calculations	
X.T. Trinh, K. Szasz, T. Hornos, K. Kawahara, J. Suda, T. Kimoto, A. Gali, E. Janzén and N.T. Son	285
Defect Levels in High Purity Semi-Insulating 4H-SiC Studied by Alpha Particle Induced Charge Transient Spectroscopy	
N. Iwamoto, S. Onoda, N. Fujita, T. Makino and T. Ohshima	289
Correlation between Microwave Reflectivity and Excess Carrier Concentrations in 4H-SiC	
M. Kato, Y. Mori and M. Ichimura	293
Diffusion of Alkali Metals in SiC	
M.K. Linnarsson and A. Hallén	297
Comparison of Carrier Lifetime Measurements and Mapping in 4H SiC Using Time Resolved Photoluminescence and μ-PCD	
B. Kallinger, M. Rommel, L. Lilja, J. Hassan, I.D. Booker, E. Janzén and J.P. Bergman	301
On Photoelectrical Properties of 6H-SiC Bulk Crystals PVT-Grown on 6H- and 4H-SiC Substrates	
G. Liaugaudas, K. Jarašiūnas, N. Tsavdaris, E. Sarigiannidou and D. Chaussende	305

3.2 Extended Defects

Basal Plane Dislocations from Inclusions in 4H-SiC Epitaxy	
R.E. Stahlbush, N.A. Mahadik and M.J. O'Loughlin	309

Photoluminescence Imaging and Discrimination of Threading Dislocations in 4H-SiC Epilayers	313
M. Nagano, I. Kamata and H. Tsuchida	
Polarized Photoluminescence from Partial Dislocations in 4H-SiC	319
R. Hirano, M. Tajima, H. Tsuchida, K.M. Itoh and K. Maeda	
Post-Growth Reduction of Basal Plane Dislocations by High Temperature Annealing in 4H-SiC Epilayers	324
N.A. Mahadik, R.E. Stahlbush, A. Nath, M.J. Tadjer, E.A. Imhoff, B.N. Feygelson and R. Nipoti	
Measurement of Critical Thickness for the Formation of Interfacial Dislocations and Half Loop Arrays in 4H-SiC Epilayer via X-Ray Topography	328
H.H. Wang, F.Z. Wu, M. Dudley, B. Raghorthamachar, G.Y. Chung, J. Zhang, B. Thomas, E. Sanchez, S.G. Mueller, D.M. Hansen and M.J. Loboda	
Study of V and Y Shape Frank-Type Stacking Faults Formation in 4H-SiC Epilayer	332
H.H. Wang, F.Z. Wu, S.Y. Byrapa, Y. Yang, B. Raghorthamachar, M. Dudley, G.Y. Chung, J. Zhang, B. Thomas, E. Sanchez, S.G. Mueller, D.M. Hansen and M.J. Loboda	
Three-Dimensional Imaging of Extended Defects in 4H-SiC by Optical Second-Harmonic Generation	338
R. Tanuma and H. Tsuchida	
Driving Force of Stacking Fault Expansion in 4H-SiC PN Diode by <i>In Situ</i> Electroluminescence Imaging	342
K. Konishi, S. Yamamoto, S. Nakata, Y. Toyoda and S. Yamakawa	
Dislocation Revelation for 4H-SiC by Using Vaporized NaOH: A Possible Way to Distinguish Edge, Screw and Mixed Threading Dislocations by Etch Pit Method	346
Y.Z. Yao, Y. Ishikawa, Y. Sugawara, K. Sato, K. Danno, H. Suzuki, H. Sakamoto, T. Bessho, S. Yamaguchi and K. Nishikawa	
TEM Observation of Defect Structure of Low-Energy Ion Implanted SiC	350
T. Kameda, A. Tomita, T. Matsui and T. Isshiki	
Structure and Origin of Carrot Defects on 4H-SiC Homoepitaxial Layers	354
L. Dong, G.S. Sun, J. Yu, G.G. Yan, W.S. Zhao, L. Wang, X.H. Zhang, X.G. Li and Z.G. Wang	
Dislocation Analysis of 4H-SiC Using KOH Low Temperature Etching	358
T. Sato, Y. Suzuki, H. Ito, T. Isshiki and M. Fukui	
Characterization of Damage Induced by Electric Discharge Machining and Wiresawing with Loose Abrasive at Subsurface of SiC Crystal	362
Y. Ishikawa, Y.Z. Yao, K. Sato, Y. Sugawara, Y. Okamoto and N. Hayashi	
Characterization of Threading Edge Dislocation in 4H-SiC by X-Ray Topography and Transmission Electron Microscopy	366
Y. Sugawara, Y.Z. Yao, Y. Ishikawa, K. Danno, H. Suzuki, T. Bessho, S. Yamaguchi, K. Nishikawa and Y. Ikuhara	
Microstructural Analysis of Damaged Layer Introduced during Chemo-Mechanical Polishing	370
H. Sako, T. Yamashita, K. Tamura, M. Sasaki, M. Nagaya, T. Kido, K. Kawata, T. Kato, K. Kojima, S. Tsukimoto, H. Matsuhata and M. Kitabatake	
Origin Analyses of Trapezoid-Shape Defects in 4-Deg.-off 4H-SiC Epitaxial Wafers by Synchrotron X-Ray Topography	374
T. Yamashita, H. Matsuhata, Y. Miyasaka, K. Momose, T. Sato and M. Kitabatake	
Micro-Raman Characterization of 4H-SiC Stacking Faults	378
N. Piluso, M. Camarda, R. Anzalone and F. La Via	
Defects Grouping and Characterizations of PL-Imaging Methods for 4H-SiC Epitaxial Layers	382
M. Odawara, K. Kamei, Y. Miyasaka, T. Yamashita, S. Takahashi, Y. Kageshima, K. Momose, H. Osawa and T. Sato	
Characterization of Vacant Broken Line Defects in A-Face Grown Crystals of Silicon Carbide	386
N. Sugiyama, M. Yamada, Y. Urakami, M. Kobayashi, T. Masuda, K. Shigetoh, I. Gunjishima, F. Hirose and S. Onda	
Formation of Double Stacking Faults from Polishing Scratches on 4H-SiC (0001) Substrate	390
S. Ushio, T. Fujimoto, H. Tsuge, M. Katsuno, S. Sato, K. Tani, H. Hirano and T. Yano	
Nanomechanical Analysis of Triangular Defect in 4H-SiC Epilayer	394
Y.J. Shin, S.I. Kim, H.J. Jung, C.W. Lee and W. Bahng	

Analysis on Generation of Localized Step-Bunchings on 4H-SiC(0001)Si Face by Synchrotron X-Ray Topography

M. Sasaki, K. Tamura, H. Sako, M. Kitabatake, K. Kojima and H. Matsuhata

398

Non Destructive Inspection of Dislocations in SiC Wafer by Mirror Projection Electron Microscopy

T. Isshiki and M. Hasegawa

402

3.3 Surface and Interface

Nanoscale Characterization of SiC Interfaces and Devices

F. Giannazzo, P. Fiorenza, M. Saggio and F. Roccaforte

407

C-Face Interface Defects in 4H-SiC MOSFETs Studied by Electrically Detected Magnetic Resonance

T. Umeda, M. Okamoto, R. Arai, Y. Satoh, R. Kosugi, S. Harada, H. Okumura, T. Makino and T. Ohshima

414

Accurate Characterization of Interface State Density of SiC MOS Structures and the Impacts on Channel Mobility

H. Yoshioka, T. Nakamura, J. Senzaki, A. Shimozato, Y. Tanaka, H. Okumura and T. Kimoto

418

Deep-Level Transient Spectroscopy Characterization of Interface States in SiO₂/4H-SiC Structures Close to the Conduction Band Edge

T. Hatakeyama, M. Sometani, K. Fukuda, H. Okumura and T. Kimoto

424

Low Frequency Noise Analysis of Monolithically Fabricated 4H-SiC CMOS Field Effect Transistors

L.C. Martin, H.K. Chan, D.T. Clark, E.P. Ramsay, A.E. Murphy, D.A. Smith, R.F. Thompson, R.A.R. Young, J.P. Goss, N.G. Wright and A.B. Horsfall

428

Estimation of Surface Recombination Velocities for n-Type 4H-SiC Surfaces Treated by Various Processes

Y. Mori, M. Kato and M. Ichimura

432

Drain-Current Deep Level Transient Spectroscopy Investigation on Epitaxial Graphene/6H-SiC Field Effect Transistors

S. Roensch, S. Hertel, S.A. Reshanov, A. Schöner, M. Krieger and H.B. Weber

436

Single Event Gate Rupture in SiC MOS Capacitors with Different Gate Oxide Thicknesses

M. Deki, T. Makino, K. Kojima, T. Tomita and T. Ohshima

440

3.4 Stress and Mechanical Properties

Mechanical Properties and Residual Stress of Thin 3C-SiC(111) Films Determined Using MEMS Structures

B. Hähnlein, M. Stubenrauch, S. Michael and J. Pezoldt

444

Influence of P⁺-Implantation and Post-Annealing on Warpage Structure of 4H-SiC Wafers

K. Ishiji, S. Kawado, Y. Hirai and S. Nagamachi

449

Residual Stress Measurements of 4H-SiC Crystals Using X-Ray Diffraction

M. Nakabayashi, T. Fujimoto, H. Tsuge, K. Kojima, K. Abe and K. Shimomura

453

Evaluation of Mechanical and Optical Properties of Hetero-Epitaxial Single Crystal 3C-SiC Squared-Membrane

R. Anzalone, G. D'Arrigo, M. Camarda, N. Piluso and F. La Via

457

3.5 Fundamental Properties

Temperature Dependence of Impact Ionization Coefficients in 4H-SiC

H. Niwa, J. Suda and T. Kimoto

461

Improved Analytical Expressions for Avalanche Breakdown in 4H-SiC

Z. Stum, Y. Tang, H. Naik and T.P. Chow

467

High-Resolution Raman and Luminescence Spectroscopy of Isotope-Pure ²⁸Si¹²C, Natural and ¹³C – Enriched 4H-SiC

I.G. Ivanov, M. Yazdanfar, B. Lundqvist, J.T. Chen, J. Hassan, P. Stenberg, R. Liljedahl, N.T. Son, J.W. Ager, O. Kordina and E. Janzén

471

Carrier Density Dependence of Fano Type Interference in Raman Spectra of p-type 4H-SiC

T. Mitani, S. Nakashima, M. Tomobe, S. Ji, K. Kojima and H. Okumura

475

Crystallographic Structure of 8H- and 10H-SiC Analyzed by Raman Spectroscopy and Diffraction Methods	479
T. Hatayama, R. Hori, H. Yano and T. Fuyuki	
Hall Factor Calculation for the Characterization of Transport Properties in N-Channel 4H-SiC MOSFETs	483
V. Uhnevionak, A. Burenkov, C. Strenger, V. Mortet, E. Bedel-Pereira, F. Cristiano, A.J. Bauer and P. Pichler	
Temperature and Electrical Field Dependence of the Ambipolar Mobility in N-Doped 4H-SiC	487
A. Hürner, C. Bonse, G. Clemmer, B. Kallinger, T. Heckel, T. Erlbacher, H. Mitlehner, V. Häublein, A.J. Bauer and L. Frey	
High-Sensitivity High-Resolution Full-Wafer Imaging of the Properties of Large n-Type SiC Using the Relative Reflectance of Two Terahertz Waves	491
A. Hamano, S. Ohno, H. Minamide, H. Ito and Y. Usuki	
Theoretical Investigation of the Single Photon Emitter Carbon Antisite-Vacancy Pair in 4H-SiC	495
V. Ivády, I.A. Abrikosov, E. Janzén and Á. Gali	
First Principles Investigation of Divacancy in SiC Polytypes for Solid State Qubit Application	499
K. Szasz, V. Ivády, E. Janzén and Á. Gali	
Impact of Carrier Lifetime on Efficiency of Photolytic Hydrogen Generation by p-Type SiC	503
K. Miyake, T. Yasuda, M. Kato, M. Ichimura, T. Hatayama and T. Ohshima	
Direct Observation of the Edge Termination of Surface Steps on 4H/6H-SiC {0001} by Tilted Low-Voltage Scanning Electron Microscopy	507
K. Ashida, T. Kajino, Y. Kutsuma, N. Ohtani and T. Kaneko	

Chapter 4: Processing of SiC

4.1 MOS Processing, SiC-SiO₂ Interfaces and Other Dielectrics

Thin PSG Process for 4H-SiC MOSFET	513
Y.K. Sharma, A.C. Ahyi, T. Isaacs-Smith, A. Modic, Y. Xu, E. Granfukel, M.R. Jennings, C. Fisher, S.M. Thomas, P.A. Mawby, S. Dhar, L.C. Feldman and J. Williams	
Depletion-Mode TDDB for n-Type MOS Capacitors of 4H-SiC	517
T. Watanabe, S. Hino, Y. Ebiike, N. Miura, M. Imaizumi and S. Yamakawa	
Threshold Voltage Instability of SiC-MOSFETs on Various Crystal Faces	521
J. Senzaki, A. Shimozato, K. Kojima, S. Harada, K. Ariyoshi, T. Kojima, Y. Tanaka and H. Okumura	
Low Energy Proton Radiation Impact on 4H-SiC nMOSFET Gate Oxide Stability	525
M. Florentin, M. Alexandru, A. Constant, B. Schmidt, J. Millan and P. Godignon	
Unexpected Effect of Thermal Storage Observed on SiC Power DMOSFET	529
Z. Chbili, P.R. Shreshta, J.P. Campbell, J.S. Suehle, D.E. Ioannou and K.P. Cheung	
Radiation-Induced Trapped Charging Effects in SiC Power MOSFETs	533
R. Green, A. Lelis, D.P. Urciuoli, M. Litz and J. Carroll	
Reliability Improvement and Optimization of Trench Orientation of 4H-SiC Trench-Gate Oxide	537
T. Kojima, S. Harada, K. Ariyoshi, J. Senzaki, M. Takei, Y. Yonezawa, Y. Tanaka and H. Okumura	
Degradation of SiO₂/SiC Interface Properties due to Mobile Ions Intrinsically Generated by High-Temperature Hydrogen Annealing	541
A. Chanthaphan, T. Hosoi, Y. Nakano, T. Nakamura, T. Shimura and H. Watanabe	
Reliability of Gate Oxides on 4H-SiC Epitaxial Surface Planarized by CMP Treatment	545
K. Yamada, O. Ishiyama, K. Tamura, T. Yamashita, A. Shimozato, T. Kato, J. Senzaki, H. Matsuhata and M. Kitabatake	
Characterization of La_xHf_yO Gate Dielectrics in 4H-SiC MOS Capacitor	549
J.H. Xia, D.M. Martin, S.S. Suvanam, C. Zetterling and M. Östling	
Si Emission into the Oxide Layer during Oxidation of Silicon Carbide	553
Y. Hijikata, Y. Akasaka, S. Yagi and H. Yaguchi	

High Mobility 4H-SiC MOSFETs Using Lanthanum Silicate Interface Engineering and ALD Deposited SiO₂ X.Y. Yang, B.M. Lee and V. Misra	557
Retarded Oxide Growth on 4H-SiC(0001) Substrates due to Sacrificial Oxidation T. Hosoi, Y. Uenishi, Y. Nakano, T. Nakamura, T. Shimura and H. Watanabe	562
Nano-Scale Native Oxide on 6H-SiC Surface and its Effect on the Ni/Native Oxide/SiC Interface Band Bending W. Huang, X. Liu, X.C. Liu, T.Y. Zhou, S.Y. Zhuo, Y.Q. Zheng, J.H. Yang and E.W. Shi	566
MOS Interfacial Studies Using Hall Measurement and Split C-V Measurement in n-Channel Carbon-Face 4H-SiC MOSFET S. Ono, E. Waki, M. Arai, K. Yamasaki and S. Takagi	571
Reduction of Density of 4H-SiC / SiO₂ Interface Traps by Pre-Oxidation Phosphorus Implantation T. Sledziewski, A. Mikhaylov, S.A. Reshanov, A. Schöner, H.B. Weber and M. Krieger	575
Conduction Mechanism of Leakage Current in Thermal Oxide on 4H-SiC M. Sometani, D. Okamoto, S. Harada, H. Ishimori, S. Takasu, T. Hatakeyama, M. Takei, Y. Yonezawa, K. Fukuda and H. Okumura	579
Systematic Analysis of the High- and Low-Field Channel Mobility in Lateral 4H-SiC MOSFETs C. Strenger, V. Uhnevionak, V. Mortet, G. Ortiz, T. Erlbacher, A. Burenkov, A.J. Bauer, F. Cristiano, E. Bedel-Pereira, P. Pichler, H. Ryssel and L. Frey	583
Experimental Studies on Water Vapor Plasma Oxidation and Thermal Oxidation of 4H-SiC (0001) for Clarification of the Atomic-Scale Flattening Mechanism in Plasma Assisted Polishing H. Deng, K. Endo and K. Yamamura	587
Rapid Thermal Oxidation of Si-Face N and P-Type On-Axis 4H-SiC M. Florentin, J. Montserrat, P. Brosselard, A. Henry and P. Godignon	591
Influence of Diverse Post-Trench Processes on the Electrical Performance of 4H-SiC MOS Structures C.T. Banzhaf, M. Grieb, A. Trautmann, A.J. Bauer and L. Frey	595
Impact of the Oxidation Temperature on the Interface Trap Density in 4H-SiC MOS Capacitors S.M. Thomas, M.R. Jennings, Y.K. Sharma, C.A. Fisher and P.A. Mawby	599
Deep Traps in 4H-SiC MOS Capacitors Investigated by Deep Level Transient Spectroscopy E.Ö. Sveinbjörnsson and O. Gíslason	603
4H-SiC MOS Capacitors and MOSFET Fabrication with Gate Oxidation at 1400°C H. Naik and T.P. Chow	607
Step-Bunching Dependence of the Lifetime of MOS Capacitor on 4° Off-Axis Si-Face 4H-SiC Epitaxial Wafers A. Bandoh, K. Suzuki, Y. Miyasaka, H. Osawa and T. Sato	611
Nitridation Effects of Gate Oxide on Channel Properties of SiC Trench MOSFETs K. Ariyoshi, S. Harada, J. Senzaki, T. Kojima, K. Kojima, Y. Tanaka and T. Shinohe	615
NF₃ Added Oxidation of 4H-SiC(0001) and Suppression of Interface Degradation R. Hasunuma, M. Nagoshi and K. Yamabe	619
Characterization of SiO₂/SiC Interfaces Annealed in N₂O or POCl₃ P. Fiorenza, L.K. Swanson, M. Vivona, F. Giannazzo, C. Bongiorno, S. Lorenti, A. Fazzetto and F. Roccaforte	623
Growth of Gate Oxides on 4H-SiC by NO at Low Partial Pressures D. Haasmann, S. Dimitrijev, J.S. Han and A. Iacopi	627
Preparation and Characterization of Nitridation Layer on 4H SiC (0001) Surface by Direct Plasma Nitridation Y. Akahane, T. Kano, K. Kimura, H. Komatsu, Y. Watanabe, T. Yamakami and K. Kamimura	631
Analysis of C-Face 4H-SiC MOS Capacitors with ZrO₂ Gate Dielectric L.S. Chan, Y.H. Chang and K.Y. Lee	635

4.2 Doping, Ion Implantation and Contacts

Applications of Vapor-Liquid-Solid Selective Epitaxy of Highly p-Type Doped 4H-SiC: PiN Diodes with Peripheral Protection and Improvement of Specific Contact Resistance of Ohmic Contacts	
N. Thierry-Jebali, M. Lazar, A. Vo-Ha, D. Carole, V. Soulière, A. Henry, D. Planson, G. Ferro, L. Konczewicz, S. Contreras, C. Brylinski and P. Brosselard	639
n- and p-Type Doping of 4H-SiC by Wet-Chemical Laser Processing	
K. Nishi, A. Ikeda, D. Marui, H. Ikenoue and T. Asano	645
Properties of Al Ohmic Contacts to n-type 4H-SiC Employing a Phosphorus-Doped and Crystallized Amorphous-Silicon Interlayer	
H. Hanafusa, A. Ohta, R. Ashihara, K. Maruyama, T. Mizuno, S. Hayashi, H. Murakami and S. Higashi	649
Microwave Annealing of Al⁺ Implanted 4H-SiC: Towards Device Fabrication	
A. Nath, A. Parisini, Y.L. Tian, M.V. Rao and R. Nipoti	653
Al⁺ Implanted 4H-SiC p⁺-i-n Diodes: Evidence for Post-Implantation-Annealing Dependent Defect Activation	
U. Grossner, F. Moscatelli and R. Nipoti	657
Temperature Dependence of Electric Conductivities in Femtosecond Laser Modified Areas in Silicon Carbide	
M. Deki, T. Oka, S. Takayoshi, Y. Naoi, T. Makino, T. Ohshima and T. Tomita	661
Comparative Study of the Current Transport Mechanisms in Ni₂Si Ohmic Contacts on n- and p-Type Implanted 4H-SiC	
M. Vivona, G. Greco, S. Di Franco, F. Giannazzo, F. Roccaforte, A. Frazzetto, S. Rascunà, E. Zanetti, A. Guarnera and M. Saggio	665
Ti/Al/Si Ohmic Contacts for both n-Type and p-Type 4H-SiC	
H. Tamaso, S. Yamada, H. Kitabayashi and T. Horii	669
Development of a Novel Cap-Free Activation Annealing Technique of 4H-SiC by Si-Vapor Ambient Annealing Using TaC/Ta Composite Materials	
S. Torimi, S. Nogami and T. Kaneko	673
Low Cost Ion Implantation Process with High Heat Resistant Photoresist in Silicon Carbide Device Fabrication	
T. Fujiwara, Y. Tanigaki, Y. Furukawa, K. Tonari, A. Otsuki, T. Imai, N. Oose, M. Utsumi, M. Ryo, M. Gotoh, S. Nakamata, T. Sakai, Y. Sakai, M. Miyajima, H. Kumura, K. Fukuda and H. Okumura	677
Characterization of Ohmic Ni/Ti/Al and Ni Contacts to 4H-SiC from -40°C to 500°C	
K. Smedfors, L. Lanni, M. Östling and C. Zetterling	681
Electrical Properties of Mg-Implanted 4H-SiC	
H. Matsuura, T. Morine and S. Nagamachi	685
Low Resistance Ohmic Contact Formation of Ni Silicide on Partially Si Ion Implanted n⁺ 4H-SiC	
W. De Silva, T. Sato, S. Kuroki and T. Kikkawa	689
On the Ti₃SiC₂ Metallic Phase Formation for Robust p-Type 4H-SiC Ohmic Contacts	
M.R. Jennings, C.A. Fisher, D. Walker, A. Sanchez, A. Pérez-Tomás, D.P. Hamilton, P.M. Gammon, S.E. Burrows, S.M. Thomas, Y.K. Sharma, F. Li and P.A. Mawby	693
Microstructure Characterization of Si/Ni Contact Layers on n-Type 4H-SiC by TEM and XEDS	
M. Wzorek, A. Czerwiński, J. Ratajczak, M.A. Borysiewicz, A.V. Kuchuk, A.B. Piotrowska and J. Kąćki	697
Effect of Shallow n-Doping on Field Effect Mobility in p-Doped Channels of 4H-SiC MOS Field Effect Transistors	
S. Noll, M. Rambach, M. Grieb, D. Scholten, A.J. Bauer and L. Frey	702
Electrical Characteristics of Schottky Contacts on Ge-Doped 4H-SiC	
M. Vivona, K. Al Assaad, V. Soulière, F. Giannazzo, F. Roccaforte and G. Ferro	706
Impact of Interface Traps on Current-Voltage Characteristics of 4H-SiC Schottky-Barrier Diodes	
H.A. Moghadam, S. Dimitrijev and J.S. Han	710
Junction Formation via Direct Bonding of Si and 6H-SiC	
Y. Sasada, T. Kurumi, H. Shimizu, H. Kinoshita and M. Yoshimoto	714
I - V Characteristics in Surface-Activated Bonding (SAB) Based Si/SiC Junctions at Raised Ambient Temperatures	
S. Nishida, J.B. Liang, M. Morimoto, N. Shigekawa and M. Arai	718

4.3 Etching, Cutting and Other Machining

4H-SiC Planarization Using Catalyst-Referred Etching with Pure Water	722
A. Isohashi, Y. Sano, S. Sadakuni and K. Yamauchi	
Investigation of the Barrier Heights for Dissociative Adsorption of HF on SiC Surfaces in the Catalyst-Referred Etching Process	726
P.V. Bui, K. Inagaki, Y. Sano, K. Yamauchi and Y. Morikawa	
Hydrogen Effects in ECR-Etching of 3C-SiC(100) Mesa Structures	730
L. Hiller, T. Stauden, R.M. Kemper, J.K.N. Lindner, D.J. As and J. Pezoldt	
Off-Orientation Influence on C-Face (0001) 4H-SiC Surface Morphology Produced by Etching Using Chlorine Trifluoride Gas	734
Y. Fukumoto, H. Habuka and T. Kato	
Development of Silicon Carbide Dry Etcher Using Chlorine Trifluoride Gas	738
D. Yajima, H. Habuka and T. Kato	
Investigation of Trenched and High Temperature Annealed 4H-SiC	742
C.T. Banzhaf, M. Grieb, A. Trautmann, A.J. Bauer and L. Frey	
Removal of Mechanical-Polishing-Induced Surface Damages on 4H-SiC Wafers by Using Chemical Etching with Molten KCl+KOH	746
Y.Z. Yao, Y. Ishikawa, Y. Sugawara and K. Sato	
Thinning of a Two-Inch Silicon Carbide Wafer by Plasma Chemical Vaporization Machining Using a Slit Electrode	750
Y. Okada, H. Nishikawa, Y. Sano, K. Yamamura and K. Yamauchi	
A Novel Grinding Technique for 4H-SiC Single-Crystal Wafers Using Triboro-Catalytic Abrasives	754
T. Kido, M. Nagaya, K. Kawata and T. Kato	
Dicing of SiC Wafer by Atmospheric-Pressure Plasma Etching Process with Slit Mask for Plasma Confinement	759
Y. Sano, H. Nishikawa, Y. Okada, K. Yamamura, S. Matsuyama and K. Yamauchi	
Multi-Wire Electrical Discharge Slicing for Silicon Carbide Part 2: Improvement on Manufacturing Wafers by Forty-Wire EDS	763
A. Itokazu, H. Miyake, T. Hashimoto and K. Fukushima	
Effects of Machining Fluid on Electric Discharge Machining of SiC Ingot	767
N. Yamamoto, S. Yamaguchi and T. Kato	
High-Speed Slicing of SiC Ingot by High-Speed Multi Wire Saw	771
H. Maeda, R. Takanabe, A. Takeda, S. Matsuda and T. Kato	
Development of Multi-Wire Electric Discharge Machining for SiC Wafer Processing	776
M. Ogawa, K. Mine, S. Fuchiyama, Y. Tawa and T. Kato	
Fabrication of Electrostatically Actuated 4H-SiC Microcantilever Resonators by Using n/p/n Epitaxial Structures and Doping-Selective Electrochemical Etching	780
K. Sato, K. Adachi, H. Okamoto, H. Yamaguchi, T. Kimoto and J. Suda	
Characteristics of a Schottky Barrier Diode and the SiC Wafers Sliced by Wire Electrical Discharge Machining	784
H. Miyake, N. Tomita, Y. Nakaki, T. Furusho, A. Itokazu, T. Hashimoto, Y. Toyoda, S. Yamakawa, H. Sumitani, T. Kuroiwa and T. Sato	

Chapter 5: Devices and Circuits

5.1 Schottky Barrier Diodes

Designing and Fabrication of the VLD Edge Termination for 3.3 kV SiC SBD	791
K. Ebihara, Y. Yamamoto, Y. Nakaki, S. Aya, S. Nakata, M. Imaizumi, Y. Toyoda and S. Yamakawa	
Study of 4H-SiC Schottky Diode Designs for 3.3kV Applications	795
H. Bartolf, V. Sundaramoorthy, A. Mihaila, M. Berthou, P. Godignon and J. Millan	
Simulation, Fabrication and Characterization of 4500V 4H-SiC JBS Diode	800
R.H. Huang, G. Chen, S. Bai, R. Li, Y. Li and Y.H. Tao	
Evaluation of Buried Grid JBS Diodes	804
J.K. Lim, D. Peftitsis, D.P. Sadik, M. Bakowski and H.P. Nee	

High Voltage SiC JBS Diodes with Multiple Zone Junction Termination Extension Using Single Etching Step

X.C. Deng, C.Y. Rao, J. Wei, H.P. Jiang, M.M. Chen, X.D. Wang and B. Zhang 808

The Fabrication of 4H-SiC Floating Junction SBDs (FJ-SBDs)

H. Yuan, X.Y. Tang, Y.M. Zhang, Y.M. Zhang, H.L. Lv, Y.H. Wang, Y.F. Zhou and Q.W. Song 812

dI_{DS}/dt

S. Jahdi, O. Alatise and P.A. Mawby 816

Properties of a SiC Schottky Barrier Diode Fabricated with a Thin Substrate

Y. Nakanishi, T. Tominaga, H. Okabe, Y. Suehiro, K. Sugahara, T. Kuroiwa, Y. Toyoda, S. Yamakawa, H. Murasaki, K. Kobayashi and H. Sumitani 820

4H-SiC Diode Avalanche Breakdown Voltage Estimation by Simulation and Junction Termination Extension Analysis

H. Rong, Y.K. Sharma, F. Li, M.R. Jennings and P.A. Mawby 824

Investigation of Stacking Faults Affecting on Reverse Leakage Current of 4H-SiC Junction Barrier Schottky Diodes Using Device Simulation

J. Hasegawa, K. Konishi, Y. Nakamura, K. Ohtsuka, S. Nakata, Y. Nakamine, T. Nishimura and M. Hatano 828

5.2 PiN Diodes

Ultrahigh-Voltage (> 20 kV) SiC PiN Diodes with a Space-Modulated JTE and Lifetime Enhancement Process via Thermal Oxidation

N. Kaji, H. Niwa, J. Suda and T. Kimoto 832

Fabrication and Design of 10 kV PiN Diodes Using On-Axis 4H-SiC

A. Salemi, B. Buono, A. Hallén, J. Hassan, P. Bergman, C. Zetterling and M. Östling 836

High Voltage and Fast Switching Reverse Recovery Characteristics of 4H-SiC PiN Diode

K. Nakayama, S. Ogata, T. Hayashi, T. Hemmi, A. Tanaka, T. Izumi, K. Asano, D. Okamoto, Y. Tanaka, T. Mizushima, M. Yoshikawa, H. Fujisawa, K. Takenaka, M. Takei, Y. Yonezawa, K. Fukuda and H. Okumura 841

Development of SiC Super-Junction (SJ) Devices by Multi-Epitaxial Growth

R. Kosugi, Y. Sakuma, K. Kojima, S. Itoh, A. Nagata, T. Yatsuo, Y. Tanaka and H. Okumura 845

V_F Degradation of 4H-SiC PiN Diodes Using Low-BPD Wafers

C. Ota, J. Nishio, K. Takao and T. Shinohe 851

13-kV, 20-A 4H-SiC PiN Diodes for Power System Applications

D. Okamoto, Y. Tanaka, T. Mizushima, M. Yoshikawa, H. Fujisawa, K. Takenaka, S. Harada, S. Ogata, T. Hayashi, T. Izumi, T. Hemmi, A. Tanaka, K. Nakayama, K. Asano, K. Matsumoto, N. Ohse, M. Ryo, C. Ota, K. Takao, M. Mizukami, T. Kato, M. Takei, Y. Yonezawa, K. Fukuda and H. Okumura 855

Variant of Excess Current in 4H-SiC pn Structures

A.M. Strel'chuk, E.V. Kalinina, A.A. Lebedev, I.K. Boricheva and V.V. Pavshukov 859

The Cryogenic Testing and Characterisation of SiC Diodes

P.M. Gammon, C.A. Fisher, V.A. Shah, M.R. Jennings, A. Pérez-Tomás, S.E. Burrows, M. Myronov, D.R. Leadley and P.A. Mawby 863

Comparison of 5kV SiC JBS and PiN Diodes

M. Berthou, P. Godignon, J. Calvo, A. Mihaila, E. Bianda and I. Nistor 867

5.3 JFETs and SITs

650V SiC JFET for High Efficiency Applications

W. Bergner, R. Rupp, U. Kirchner and D. Kueck 871

Gate-Drive Voltage Design for 600-V Vertical-Trench Normally-Off SiC JFETs toward 94% Efficiency Server Power Supply

S. Akiyama, K. Katoh, H. Shimizu, A. Hatanaka, T. Ogawa, N. Yokoyama and K. Ishikawa 875

Evaluation of SiC Stack Cascode for 200°C Operations

X.Q. Li, P. Alexandrov, J. Hostetler and A. Bhalla 879

Beam Acceleration Experiment with SiC Based Power Supply and the Next Generation SiC-JFET Package

K. Okamura, Y. Osawa, M. Wake, T. Yoshimoto, R. Sasaki, K. Takaki and K. Takayama 883

The Role of Substrate Compensation on DC Characteristics of 4H-SiC MESFET with Buffer Layer: A Combined Two-Dimensional Simulations and Analytical Study	887
M.H.L. Rao and N.V.L.N. Murty	
Monolithic Integration of Power MESFET for High Temperature SiC Integrated Circuits	891
V. Banu, J. Montserrat, M. Alexandru, X. Jordá, J. Millan and P. Godignon	
SiC Current Limiting FETs (CLFs) for DC Applications	895
D. Tournier, P. Godignon, S.Q. Niu and J.F. de Palma	
3 kV Normally-Off 4H-SiC Buried Gate Static Induction Transistors (SiC-BGSITs)	899
A. Takatsuka, Y. Tanaka, K. Yano, N. Matsumoto, T. Yatsuo and K. Arai	

5.4 MOSFETs

1700V, 5.5mOhm·cm² 4H-SiC DMOSFET with Stable 225°C Operation	903
K. Matocha, K. Chatty, S. Banerjee and L.B. Rowland	
A Novel Truncated V-Groove 4H-SiC MOSFET with High Avalanche Breakdown Voltage and Low Specific on-Resistance	907
T. Masuda, K. Wada, T. Hiyoshi, Y. Saito, H. Tamaso, M. Sakai, K. Hiratsuka, Y. Mikamura, M. Nishiguchi, T. Hatayama and H. Yano	
40mΩ / 1700V DiomOS (Diode in SiC MOSFET) for High Power Switching Applications	911
A. Ohoka, N. Horikawa, T. Kiyosawa, H. Sorada, M. Uchida, Y. Kanzawa, K. Sawada, T. Ueda and E. Fujii	
Blocking Characteristics of 2.2 kV and 3.3 kV-Class 4H-SiC MOSFETs with Improved Doping Control for Edge Termination	915
K. Wada, K. Uchida, R. Kimura, M. Sakai, S. Hatsukawa, K. Hiratsuka, N. Hirakata and Y. Mikamura	
4H-SiC Trench MOSFET with Bottom Oxide Protection	919
Y. Kagawa, N. Fujiwara, K. Sugawara, R. Tanaka, Y. Fukui, Y. Yamamoto, N. Miura, M. Imaizumi, S. Nakata and S. Yamakawa	
SiC Trench MOSFET with an Integrated Low Von Unipolar Heterojunction Diode	923
W. Ni, K. Emori, T. Marui, Y. Saito, S. Yamagami, T. Hayashi and M. Hoshi	
SiC Epi-Channel Lateral MOSFETs	927
C.T. Yen, M. Bakowski, C.C. Hung, S.A. Reshanov, A. Schöner, C.Y. Lee, L.S. Lee, J.H. Wei, T.Y. Chiu and C.F. Huang	
600 V -Class V-Groove SiC MOSFETs	931
Y. Saito, M. Furumai, T. Hiyoshi, K. Wada, T. Masuda, K. Hiratsuka, Y. Mikamura and T. Hatayama	
14.6 mΩcm² 3.3 kV DIMOSFET on 4H-SiC (000-1)	935
H. Kono, M. Furukawa, K. Ariyoshi, T. Suzuki, Y. Tanaka and T. Shinohe	
1200 V 4H-SiC DMOSFET with an Integrated Gate Buffer	939
S.H. Ryu, C. Jonas, C. Capell, Y. Lemma, A. Agarwal, T. McNutt, D. Grider, S.T. Allen and J.W. Palmour	
Designing of Quasi-Modulated Region in 4H-SiC Lateral RESURF MOSFETs	943
Y. Nanen, J. Suda and T. Kimoto	
Utilization of SiC MOSFET Body Diode in Hard Switching Applications	947
A. Bolotnikov, J. Glaser, J. Nasadoski, P. Losee, S. Klopman, A. Permy and L. Stevanovic	
Development of 3.3 kV SiC-MOSFET: Suppression of Forward Voltage Degradation of the Body Diode	951
S. Yamamoto, Y. Nakao, N. Tomita, S. Nakata and S. Yamakawa	
High Temperature Reliability of the SiC-MOSFET with Copper Metallization	955
H. Okabe, M. Yoshida, T. Tominaga, J. Fujita, K. Endo, Y. Yokoyama, K. Nishikawa, Y. Toyoda and S. Yamakawa	
Impact of Hot Carrier Degradation and Positive Bias Temperature Stress on Lateral 4H-SiC nMOSFETs	959
G. Pobegen, T. Aichinger, A. Salinaro and T. Grasser	
Investigation on Internally Unbalanced Switching Behavior for Realization of 1-cm² SiC-MOSFET	963
S. Hino, M. Ito, N. Miura, M. Imaizumi and S. Yamakawa	
Reliability Performance of 1200 V and 1700 V 4H-SiC DMOSFETs for Next Generation Power Conversion Applications	967
D.A. Gajewski, S.H. Ryu, M. Das, B. Hull, J. Young and J.W. Palmour	

Comparison of 600V Si, SiC and GaN Power Devices S. Chowdhury, Z. Stum, Z.D. Li, K. Ueno and T.P. Chow	971
Improvement of Channel Mobility in 4H-SiC C-Face MOSFETs by H₂ Rich Wet Re-Oxidation M. Okamoto, Y. Makifuchi, T. Araoka, M. Miyazato, Y. Sugahara, T. Tsutsumi, Y. Onishi, H. Kimura, S. Harada, K. Fukuda, A. Otsuki and H. Okumura	975
Electrical Characteristics/Reliability Affected by Defects Analyzed by the Integrated Evaluation Platform for SiC Epitaxial Films M. Kitabatake, H. Sako, M. Sasaki, T. Yamashita, K. Tamura, K. Yamada, O. Ishiyama, J. Senzaki and H. Matsuhata	979
Novel Gate Oxide Process for Realization of High Threshold Voltage in 4H-SiC MOSFET M. Furuhashi, T. Tanioka, M. Imaizumi, N. Miura and S. Yamakawa	985
Comparative Study of 4H-SiC DMOSFETs with N₂O Thermal Oxide and Deposit Oxide with Post Oxidation Anneal C.T. Yen, C.C. Hung, A. Mikhaylov, C.Y. Lee, L.S. Lee, J.H. Wei, T.Y. Chiu, C.F. Huang, S.A. Reshanov and A. Schöner	989
Characterization of SiO₂/4H-SiC Interface by Device Simulation and Temperature Dependence of On-Resistance of SiC MOSFET K. Ohtsuka, S. Hino, A. Nagae, R. Tanaka, Y. Kagawa, N. Miura and S. Nakata	993
Selection of SPICE Parameters and Equations for Effective Simulation of Circuits with 4H-SiC Power MOSFETs P. Tanner, S. Dimitrijev, H.A. Moghadam, A. Aminbeidokhti and J.S. Han	997

5.5 Bipolar Junction Transistors

Rapidly Maturing SiC Junction Transistors Featuring Current Gain (β) > 130, Blocking Voltages up to 2700 V and Stable Long-Term Operation S.G. Sundaresan, S. Jeliazkov, B. Grummel and R. Singh	1001
SiC Etching and Sacrificial Oxidation Effects on the Performance of 4H-SiC BJTs L. Lanni, B.G. Malm, M. Östling and C. Zetterling	1005
Modeling of High Performance 4H-SiC Emitter Coupled Logic Circuits S. Singh, N. El Sayed, H. Elgabra, T. ElBoshra, M. Wahbah and M. Al Zaabi	1009
Characterization of 4H-SiC Bipolar Junction Transistor at High Temperatures N. Zhang, Y. Rao, N. Xu, A. Maralani and A.P. Pisano	1013
Stability of Current Gain in SiC BJTs B. Buono, F. Allerstam, M. Domeij, A. Konstantinov, K. Gumaelius, H. Das and T. Neyer	1017

5.6 Thyristors

Optical Triggering of High Current (1300 A), High-Voltage (12 kV) 4H-SiC Thyristor S. Rumyantsev, M.E. Levenshtein, M. Shur, L. Cheng, A.K. Agarwal and J.W. Palmour	1021
Static and Dynamic Performance Evaluation of >13 kV SiC-ETO and its Application as a Solid-State Circuit Breaker M.A. Rezaei, G.Y. Wang, A.Q. Huang, L. Cheng, J.W. Palmour and C. Scozzie	1025

5.7 IGBTs

20 kV 4H-SiC N-IGBTs S.H. Ryu, C. Capell, C. Jonas, M.J. O'Loughlin, J. Clayton, E. van Brunt, K. Lam, J. Richmond, A. Kadavelugu, S. Bhattacharya, A.A. Burk, A. Agarwal, D. Grider, S.T. Allen and J.W. Palmour	1030
On the TCAD Based Design Diagnostic Study of 4H-SiC Based IGBTs M. Nawaz and F. Chimento	1034
Effect of Current-Spreading Layer Formed by Ion Implantation on the Electrical Properties of High-Voltage 4H-SiC p-Channel IGBTs T. Deguchi, S. Katakami, H. Fujisawa, K. Takenaka, H. Ishimori, S. Takasu, M. Takei, M. Arai, Y. Yonezawa, K. Fukuda and H. Okumura	1038

5.8 Sensors

Radiation-Induced Currents in 4H-SiC Dosimeters for Real-Time Gamma-Ray Dose Rate Monitoring	
N. Fujita, N. Iwamoto, S. Onoda, T. Makino and T. Ohshima	1042
Nuclear Radiation Detectors Based on 4H-SiC p⁺-n Junction	
F. Issa, V. Vervisch, L. Ottaviani, D. Szalkai, L. Vermeeren, A. Lioussy, A. Kuznetsov, M. Lazar, A. Klix, O. Palais and A. Hallén	1046
Optical and Electrical Simulations of Solar Cell Based on Silicon and Silicon Carbide	
S. Biondo, W. Vervisch and L. Ottaviani	1050
High Temperature Hydrogen Sensor Based on Silicon Carbide (SiC) MOS Capacitor Structure	
B. Ofirim, G. Brezeanu, F. Draghici and I. Rusu	1054
Discriminating High k Dielectric Gas Sensors	
S.K. Roy, K.V. Vassilevski, C.J. O'Malley, N.G. Wright and A.B. Horsfall	1058
Two Packaging Solutions for High Temperature SiC Diode Sensors	
G. Brezeanu, F. Draghici, M. Badila, F. Craciunoiu, G. PRISTAVU, R. Pascu and F. Bernea	1063
Silicon Carbide Field Effect Transistors for Detection of Ultra-Low Concentrations of Hazardous Volatile Organic Compounds	
D. Puglisi, J. Eriksson, C. Bur, A. Schütze, A. Lloyd Spetz and M. Andersson	1067

5.9 Circuits, Packages and Systems

High Speed Rail Awaits the next Breakthrough of Power Semiconductors	
T. Uzuka and E. Masada	1071
Progress in High Voltage SiC and GaN Power Switching Devices	
T.P. Chow	1077
High-Efficiency Power Conversion Using Silicon Carbide Power Electronics	
H.P. Nee, J. Rabkowski, D. Peftitsis, G. Tolstoy, J. Colmenares, D.P. Sadik, M. Bakowski, J.K. Lim, A. Antonopoulos, L. Ängquist and M. Zdanowski	1083
Strategic Overview of High-Voltage SiC Power Device Development Aiming at Global Energy Savings	
L. Cheng, J.W. Palmour, A.K. Agarwal, S.T. Allen, E.V. Brunt, G.Y. Wang, V. Pala, W.J. Sung, A.Q. Huang, M.J. O'Loughlin, A.A. Burk, D.E. Grider and C. Scozzie	1089
SiC Power Module for Compact Power Conversion Equipment	
K. Yamashita, K. Kato, H. Ikeuchi, J. Tanaka, K. Toyota, T. Nakamura, K. Takahashi, R. Arakawa and T. Sasaoka	1096
Inverter-Rectifier Using SiC Power Devices for Bidirectional Wireless Power Transfer System of Electric Vehicles	
M. Hachisuka, T. Fukuhara, Y. Kaneko and S. Abe	1100
SiC Power Devices as Enabler for High Power Density - Aspects and Prospects	
P. Friedrichs	1104
High Temperature Resistant Packaging for SiC Power Devices Using Interconnections Formed by Ni Micro-Electroplating	
N. Kato, A. Shigenaga and K. Tatsumi	1110
Research of Silver Sintering Process and Reliability for High Temperature Operation of SiC Power Devices	
Z. Zhang, T. Nakamura and T. Hanada	1114
Pressure Dependence of Thermal Contact Resistance between Copper Heat Sink and Copper DBC Surfaces in SiC Power Device Packages	
Z. Toth Pal, T. Hammam and H.P. Nee	1118
SiC Power Devices Operation from Cryogenic to High Temperature: Investigation of Various 1.2kV SiC Power Devices	
T. Chailloux, C. Calvez, N. Thierry-Jebali, D. Planson and D. Tournier	1122
Silicon Carbide Transistors for IC Design Applications up to 600 °C	
A. Maralani, W.C. Lien, N. Zhang and A.P. Pisano	1126
High Temperature Electrical Characterization of 4H-SiC MESFET Basic Logic Gates	
M. Alexandru, V. Banu, M. Florentin, X. Jordá, M. Vellvehi and D. Tournier	1130

Chapter 6: Related Materials

6.1 Graphene

Controlling the Carrier Concentration of Epitaxial Graphene by Ultraviolet Illumination	1137
V. Eless, R. Yakimova and R. Pearce	
Electrical Nanocharacterization of Epitaxial Graphene/Silicon Carbide Schottky Contacts	1142
F. Giannazzo, S. Hertel, A. Albert, A. La Magna, F. Roccaforte, M. Krieger and H.B. Weber	
Carrier Mobility as a Function of Temperature in as-Grown and H-Intercalated Epitaxial Graphenes on 4H-SiC	
M. Winters, E.B. Thorsteinsson, E.Ö. Sveinbjörnsson, H.P. Gislason, J. Hassan, E. Janzén and N. Rorsman	1146
Stability and Reactivity of [11-20] Step in Initial Stage of Epitaxial Graphene Growth on SiC(0001)	
H. Kageshima, H. Hibino, H. Yamaguchi and M. Nagase	1150
Optimizing the Vacuum Growth of Epitaxial Graphene on 6H-SiC	
T. Hopf, K. Vassilevski, E. Escobedo-Cousin, N.G. Wright, A.G. O'Neill, A.B. Horsfall, J.P. Goss, A. Barlow, G. Wells and M. Hunt	1154
Formation of Graphene onto Atomically Flat 6H-SiC	
G. Rius, N. Mestres, Y. Tanaka, H. Miyazaki, O. Eryu and P. Godignon	1158
Solid Phase Growth of Graphene on Silicon Carbide by Nickel Silicidation: Graphene Formation Mechanisms	
E. Escobedo-Cousin, K. Vassilevski, T. Hopf, N. Wright, A.G. O'Neill, A.B. Horsfall and J.P. Goss	1162
Backside Monitoring of Graphene on Silicon Carbide by Raman Spectroscopy	
F. Fromm, M. Hundhausen, M. Kaiser and T. Seyller	1166
Ion-Beam Irradiation Effect in the Growth Process of Graphene on Silicon Carbide-on-Insulator Substrates	
M. Okano, D. Edamoto, K. Uchida, I. Omura, T. Ikari, M. Nakao and M. Naitoh	1170

6.2 III-Nitrides

Commercialization of High 600V GaN-on-Silicon Power Devices	1174
P. Parikh, Y.F. Wu and L.K. Shen	
Magnetoresistance of AlGaN/GaN High Electron Mobility Transistors on Silicon	
S. Roensch, V. Sizov, T. Yagi, S. Murad, L. Groh, S. Lutgen, M. Sickmoeller, M. Krieger and H.B. Weber	1180
Evidence of Low Temperature Decomposition of GaN Hetero-Epitaxial Layers on C-Plane Sapphire Surface Characterized by Differential Scanning Calorimetry	
N. Thierry-Jebali, R. Chiriac and C. Brylinski	1185
A Proposal to Apply Effective Acceptor Level for Representing Increased Ionization Ratio of Mg Acceptors in Extrinsic Photon-Recycled GaN	
K. Mochizuki, T. Mishima, Y. Ishida, Y. Hatakeyama, K. Nomoto, N. Kaneda, T. Tsuchiya, A. Terano, T. Tsuchiya, H. Uchiyama, S. Tanaka and T. Nakamura	1189
Planarization of the Gallium Nitride Substrate Grown by the Na Flux Method Applying Catalyst-Referred Etching	
W. Yamaguchi, S. Sadakuni, A. Isohashi, H. Asano, Y. Sano, M. Imade, M. Maruyama, M. Yoshimura, Y. Mori and K. Yamauchi	1193

6.3 Si_{1-x}C_x and ZnO

Evaluation of Degradation due to Electron Irradiation of Si_{1-x}C_x S/D n-type MOSFETs	
M. Hori, Y. Asai, M. Yoneoka, I. Tsunoda, K. Takakura, T. Nakashima, M.B. Gonzalez, E. Simoen and C. Claeys	1197
Structural Analysis of ZnO Thin Films Grown in Room Temperature on PET Film	
H. Yamamoto, K. Idehara, R. Kimura, H. Nishigaki, N. Hasuike, H. Harima and T. Isshiki	1201